## G. Device & Process Modeling, Simulation and Reliability 분과

2017년 2월 14일 (화), 16:00-17:30
Room C (사파이어, 2층)

### [TC3-G] Device Modeling and Simulation 1

좌장: 김대환(국민대학교), 최성진(국민대학교)

| | |
|---|---|
| **TC3-G-1**<br>**16:00-16:15** | **Surface Potential Model for L-shaped Tunnel Field-Effect-Transistor**<br>Faraz Najam and Yun Seop Yu<br>*Department of Electrical, Electronic and Control Engineering and IITC, Hankyong National University* |
| **TC3-G-2**<br>**16:15-16:30** | **Density-Functional Theory Based Simulation of Biaxial Strained Silicon Ultra-Thin-Body FETs**<br>Seonghyun Heo, Hyo-Eun Jung, and Mincheol Shin<br>*Department of Electrical Engineering, KAIST* |
| **TC3-G-3**<br>**16:30-16:45** | **TCAD-based Analysis on the Relationship between the Physical Parameters in charge Trapping and the Stretched Exponential Model Parameters in Amorphous InGaZnO TFTs under the Positive Gate Bias Temperature Stress**<br>Jihyun Rhee, Sungju Choi, Hara Kang, Jae-Young Kim, Jun Tae Jang, Daehyun Ko, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim<br>*School of Electrical Engineering, Kookmin University* |
| **TC3-G-4**<br>**16:45-17:00** | **Simulation Study on Drain Current Characteristics in Linear and Saturation Region of Tunnel Field Effect Transistor (TFET)**<br>Ryoongbin Lee, Dae Woong Kwon, Euyhwan Park, Junil Lee, Sihyun Kim, and Byung-Gook Park<br>*Department of Electrical and Computer Engineering, Seoul National University* |
| **TC3-G-5**<br>**17:00-17:15** | **A Development of New CDM SPICE Simulation Model**<br>Jung-woo Han, Young-chul Kim, Young-sang Son, Joong-hyeok Byeon, Joon-tae Jan, Geun-tae Kwon, and Yoon-jong Lee<br>*TE team, Dongbu HiTecks Co., Ltd.* |
| **TC3-G-6**<br>**17:15-17:30** | **TCAD-based Comparative Study on the Positive Bias Stress Instability between the Single-Gate and Double-Gate Structured In-Ga-Zn-O TFTs**<br>Sungju Choi, Jun Tae Jang, Hara Kang, Jae-Young Kim, Daehyun Ko, Jihyun Rhee, Jun Tae Jang, Hye Ri Yu, Jisun Park, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim<br>*School of Electrical Engineering, Kookmin University* |